

INFORMATION DISCLOSURE CITATION

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ATTY DOCKET NO
FIS920010293US2

SERIAL NO.
10/706,773

Edward Barth et al.

FILING 11/12/03

GROUP
2811

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
V	5,679,169	10/21/1997	Gonzales et al.	—	—	—
	6,080,529	06/27/2000	Ye et al.	—	—	—
	6,150,258	11/21/2000	Mountsler et al.	—	—	—
	6,153,523	11/28/2000	Van Ngo et al.	—	—	—
	6,184,128 B1	02/06/2001	Wang et al.	—	—	—
	6,184,572 B1	02/06/2001	Mountsier et al.	—	—	—
	6,187,672 B1	02/13/2001	Zhao et al.	—	—	—
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N	US 2001/0003064 A1	06/07/2001	Obto	—	—	—

FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
					YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

V	Soo Geun Lee et al., "Low Dielectric Constant 3MS a-SiC:H as Cu Diffusion Barrier Layer in Cu Dual Damascene Process," Japanese Journal of Applied Physics, Part 1, Vol. 40, No. 4B, pp. 2663-2668, April 2001.
V	2000 IEEE, A High performance 0.13um Copper BEOL Technology with Low-k Dielectric, R.D. Goldblatt et al., IBM Semiconductor Research and Development Center, Hopewell Junction, NY, Infineon Technologies Inc.

EXAMINER

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INFORMATION DISCLOSURE CITATION

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Docket Number (Optional)

FIS920010293US 2

Application Number

706,773

Applicant(s)

Edward Barth, et al.

Filing Date

November 12, 2003

Group Art Unit

2811
Not Yet Assigned

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
✓		6,071,809	06/2000	Zhao, Bin	—	—	—
✓		6,420,261	07/2002	Kudo, Hiroshi	—	—	—
✓		6,424,038	07/2002	Bao, et al.	—	—	—
✓		US2003/0008493	01/2003	Lee	—	—	—

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	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO
✓		WO 99/33102	7/1/1999	PCT	—	—	✓	
✓		FR2794286	12/1/2000	France	—	—	ABS	
✓		JP11330023A	11/30/1999	Japan	—	—	ABS	

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

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